

# MA2B064

## Silicon planar type trigger device

Thyristor element

### ■ Features

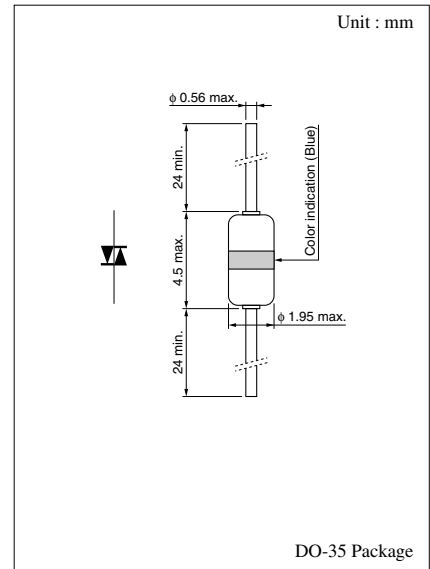
- Satisfactory symmetry of  $V_{BO}$
- Large  $V_O$  and small  $I_{BO}$

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Average total power dissipation	$P_{(AV)}$	150	mW
Peak current*1	$I_{PM}$	2.0	A
Operating ambient temperature*2	$T_{opr}$	100	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

Note) \*1 :  $T_a < 50^\circ\text{C}$ ,  $t = 10 \mu\text{s}$ , repetitive frequency 60 Hz

\*2 : Maximum ambient temperature during operation



Marking Symbol: MA2B064

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakover current	$I_{BO}$	$V = V_{BO}$			50	$\mu\text{A}$
Breakover voltage*1	$V_{BO}$	$I = I_{BO}$	28		36	V
Output voltage*1	$V_O$		4	7		V
Temperature coefficient of breakover voltage	—			0.1		$\% / ^\circ\text{C}$
Breakover voltage deviation*2	$\Delta V_{BO}$				3.5	V

Note) 1. Rated input/output frequency: 100 MHz

2. \*1 : Measurement of  $V_{BO}$  and  $V_O$

\*2 : Symmetry of  $V_{BO}$

